Silicon N-Channel MOS FET

HITACHI

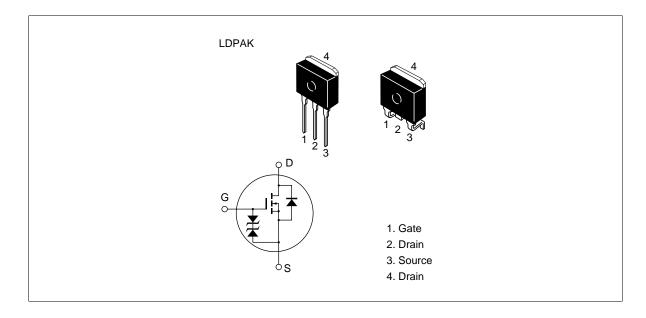
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- · Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline





Absolute Maximum Ratings $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit	
Drain to source voltage	$V_{ t DSS}$	600	V	
Gate to source voltage	V_{GSS}	±30	V	
Drain current	I _D	4	А	
Drain peak current	I _{D(pulse)} *1	16	А	
Body to drain diode reverse drain current	I _{DR}	4	Α	
Channel dissipation	Pch*2	50	W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Notes 1. PW \leq 10 μ s, duty cycle \leq 1%

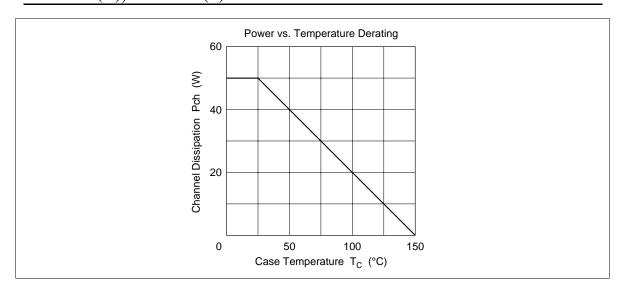
2. Value at $T_c = 25^{\circ}C$

Electrical Characteristics (Ta = 25°C)

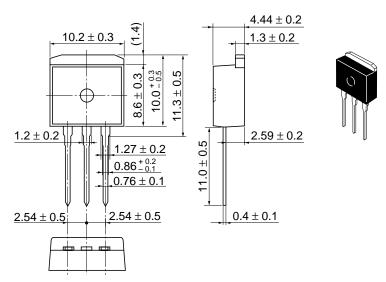
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	600	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±30	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	250	μΑ	V _{DS} = 500 V, V _{GS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	_	3.0	V	I _D = 1 mA, V _{DS} = 10 V
Static Drain to source on state resistance	$R_{\mathrm{DS(on)}}$	_	1.8	2.4	Ω	$I_D = 2 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
Forward transfer admittance	yfs	2.2	3.5	_	S	$I_D = 2 \text{ A}, V_{DS} = 10 \text{ V}^{*1}$
Input capacitance	Ciss	_	600	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	_	140	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	25	_	pF	_
Turn-on delay time	t _{d(on)}	_	8	_	ns	I _D = 2 A, V _{GS} = 10 V,
Rise time	t _r	_	30	_	ns	$R_L = 15 \Omega$
Turn-off delay time	t _{d(off)}	_	60	_	ns	
Fall time	t _f	_	35	_	ns	_
Body to drain diode forward voltage	V_{DF}	_	0.9	_	V	I _F = 4 A, V _{GS} = 0
Body to drain diode reverse recovery time	t _{rr}		300		ns	$I_F = 4 \text{ A}, V_{GS} = 0,$ $di_F/dt = 100 \text{ A/}\mu\text{s}$

Note 1. Pulse test

See characteristic curves of 2SK1402.







Hitachi Code	LDPAK (L)
JEDEC	_
EIAJ	_
Weight (reference value)	1.4 a

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